imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

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Dual Switching Diode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating	Symbol	Max	Unit	
Continuous Reverse Voltage	V _R	100	V	
Recurrent Peak Forward Current	١ _F	200	mA	
Peak Forward Surge Current Pulse Width = 10 μ s	I _{FM(surge)}	500	mA	

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Мах	Unit
Total Device Dissipation (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	357 2.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	500 4.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	250	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. FR-4 @ Minimum Pad



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CASE 463A PLASTIC

MARKING DIAGRAM



A6 = Specific Device Code

M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BAS16DXV6T1G	SOT–563 (Pb–Free)	4000 / Tape & Reel
SBAS16DXV6T1G	SOT–563 (Pb–Free)	4000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Forward Voltage $(I_F = 1.0 \text{ mA})$ $(I_F = 10 \text{ mA})$ $(I_F = 50 \text{ mA})$ $(I_F = 150 \text{ mA})$	V _F	- - - -	715 855 1000 1250	mV
Reverse Current $(V_R = 100 \text{ V})$ $(V_R = 75 \text{ V}, T_J = 150^{\circ}\text{C})$ $(V_R = 25 \text{ V}, T_J = 150^{\circ}\text{C})$	I _R	- - -	1.0 50 30	μΑ
Capacitance $(V_R = 0, f = 1.0 \text{ MHz})$	CD	-	2.0	pF
Reverse Recovery Time $(I_F = I_R = 10 \text{ mA}, R_L = 50 \Omega)$ (Figure 1)	t _{rr}	-	6.0	ns
Stored Charge (I _F = 10 mA to V _R = 6.0 V, R _L = 500 Ω) (Figure 2)	QS	-	45	PC
Forward Recovery Voltage $(I_F = 10 \text{ mA}, t_r = 20 \text{ ns})$ (Figure 3)	V _{FR}	-	1.75	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

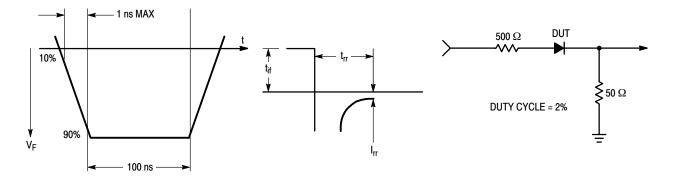


Figure 1. Reverse Recovery Time Equivalent Test Circuit

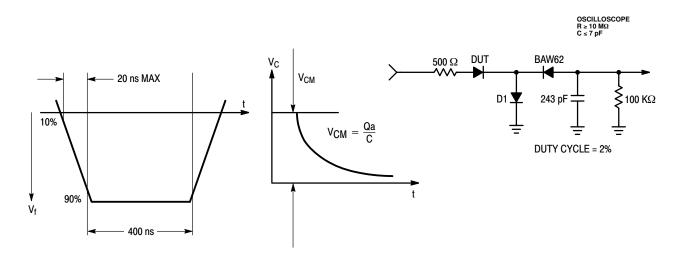


Figure 2. Stored Charge Equivalent Test Circuit

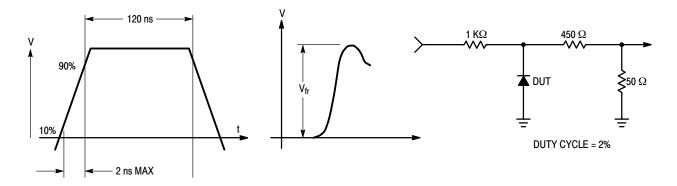


Figure 3. Forward Recovery Voltage Equivalent Test Circuit

TYPICAL CHARACTERISTICS

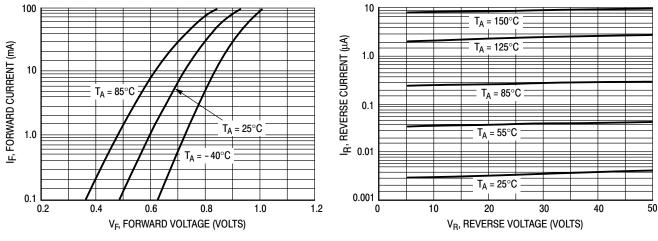


Figure 4. Forward Voltage



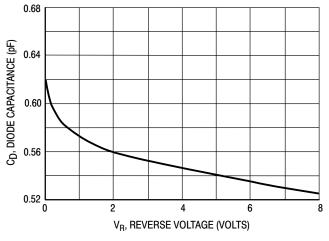
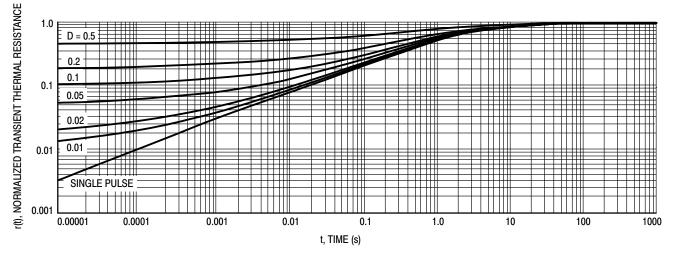
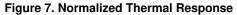


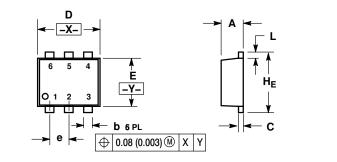
Figure 6. Capacitance





PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A ISSUE F



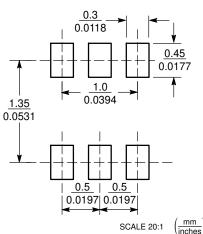
NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI V14 5M 1982

Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETERS

 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
Е	1.10	1.20	1.30	0.043	0.047	0.051
е	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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BAS16DXV6/D

STYLE 10: PIN 1. CATHODE 1 2. N/C

3. CATHODE 2 4. ANODE 2

5. N/C 6. ANODE 1

6. ANODE 1